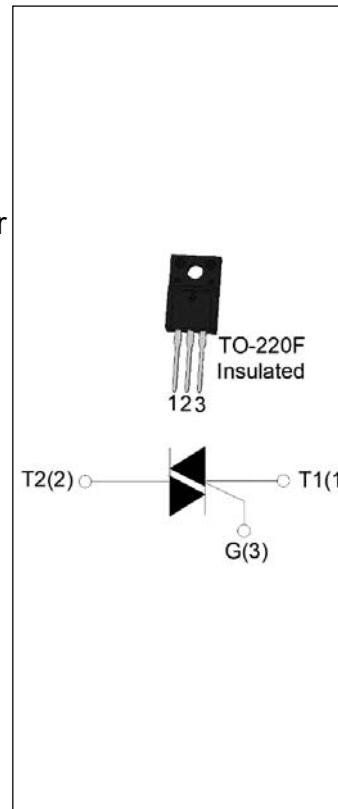


**DESCRIPTION:**

The JST16F-1200CW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST16F-1200CW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JST16F-1200CW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.

**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
$V_{DRM}/V_{RRM}$	1200	V
$I_{GT\text{ I/II/III}}$	35/35/35	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	1200	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	1200	V
RMS on-state current ( $T_c \leq 73^\circ\text{C}$ )	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	160	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		176	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	128	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	$dI/dt$	100	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.5	W

Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.7)	$V_{pp}$	4	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	35	mA
$V_{GT}$		I - II - III	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	I - II - III	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III	MAX.	50	mA
		II		60	
$I_H$	$I_T=500\text{mA}$		MAX.	40	mA
$dV/dt$	$V_D=800\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	400	V/ $\mu\text{s}$
$(dI/dt)c$	$(dV/dt)c=20\text{V}/\mu\text{s}$ $T_j=125^\circ\text{C}$		MIN.	10	A/ms
$t_{on}$	$I_G=40\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^\circ\text{C}$	TYP.		7	$\mu\text{s}$
$t_{off}$				50	

**STATIC CHARACTERISTICS**

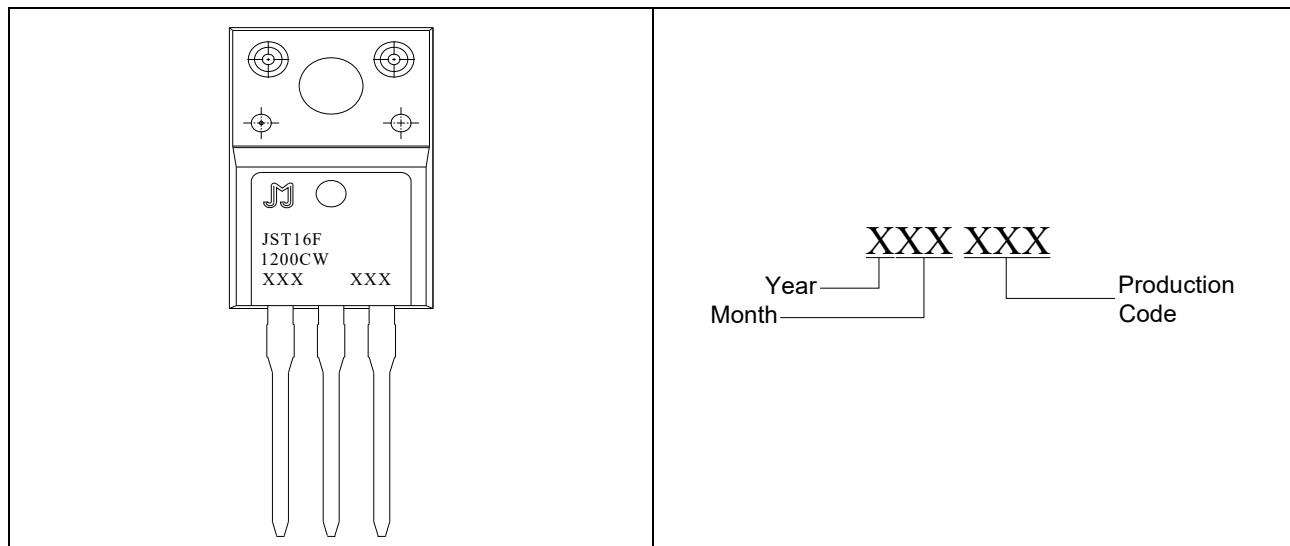
Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=22.5\text{A}$	$t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5
$V_{TO}$	Threshold voltage		$T_j=125^\circ\text{C}$	0.77
$R_D$	Dynamic resistance		$T_j=125^\circ\text{C}$	$\text{m}\Omega$
$I_{DRM}$	$V_D=V_{DRM}$	$V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	10
$I_{RRM}$			$T_j=125^\circ\text{C}$	2

**THERMAL RESISTANCES**

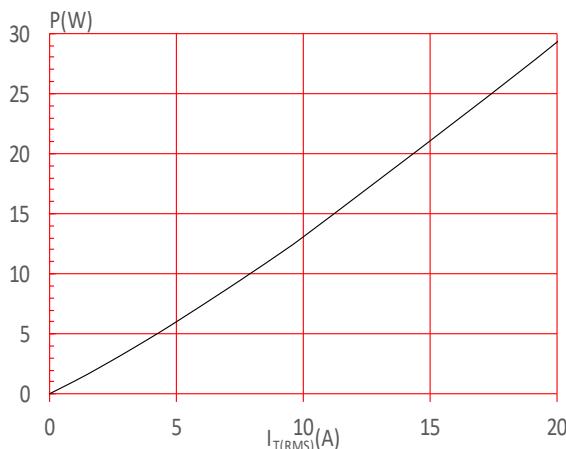
Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	2.3	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ\text{C}/\text{W}$

**ORDERING INFORMATION**

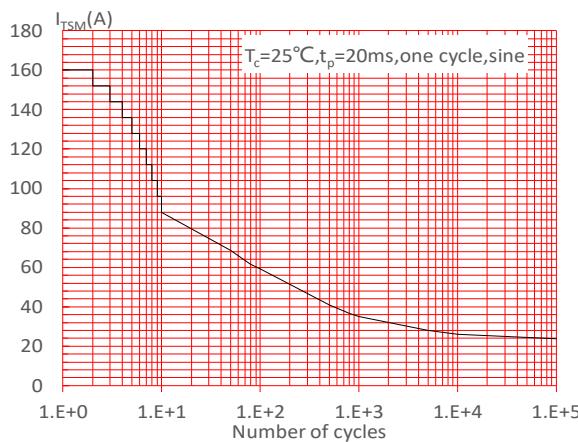
<u>J</u>	<u>ST</u>	<u>16</u>	<u>F</u>	<u>-1200</u>	<u>CW</u>
JieJie Microelectronics Co., Ltd.					
	Triacs				
		IT(RMS):16A			
			F:TO-220F(Ins)		
				CW:IGT1-3≤35mA	
				1200:V <sub>DRM</sub> / V <sub>RRM</sub> ≥ 1200V	

**MARKING**

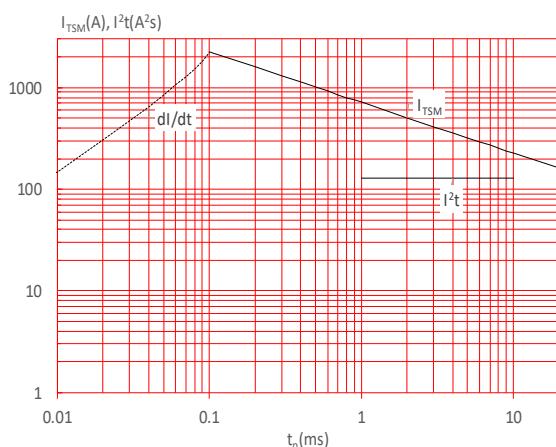
**FIG.1** Maximum power dissipation versus RMS on-state current



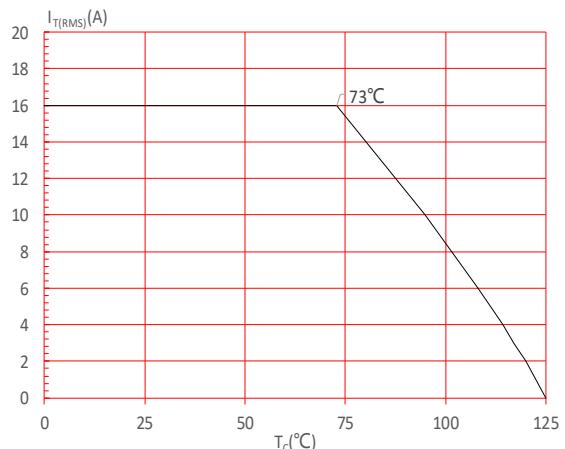
**FIG.3:** Surge peak on-state current versus number of cycles



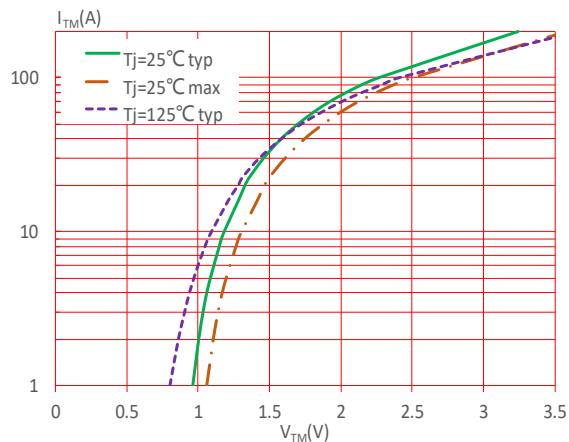
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $dI/dt < 100\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

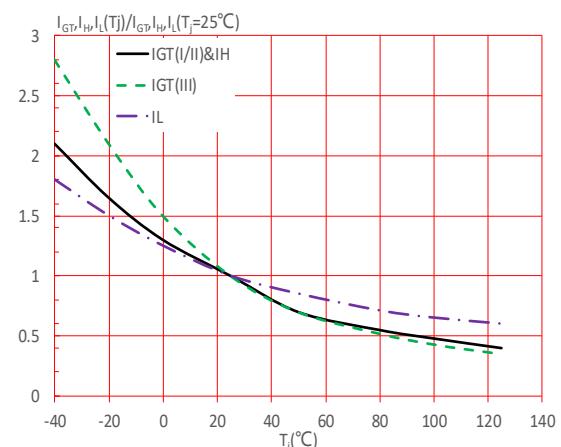
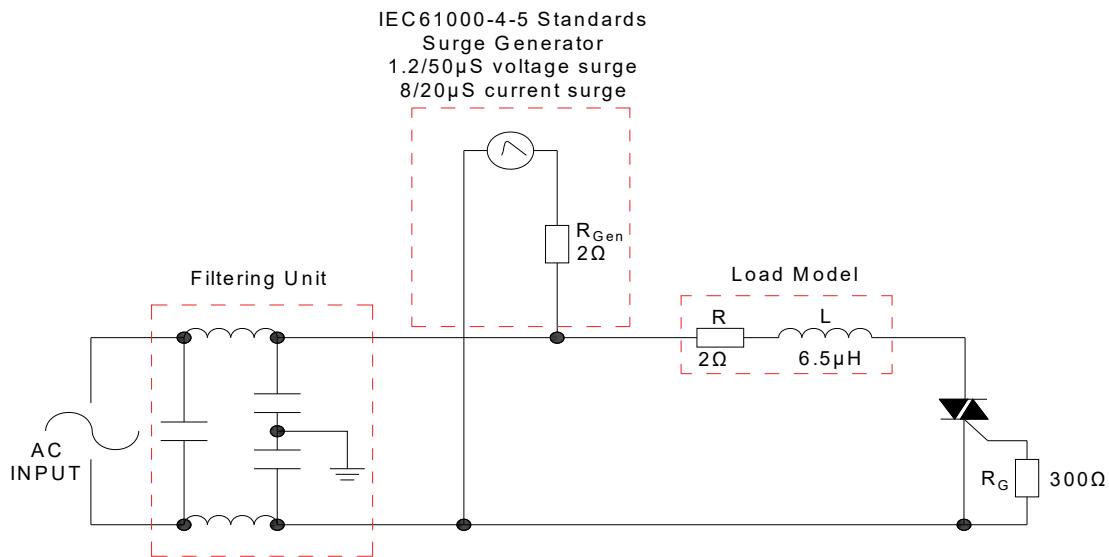


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie

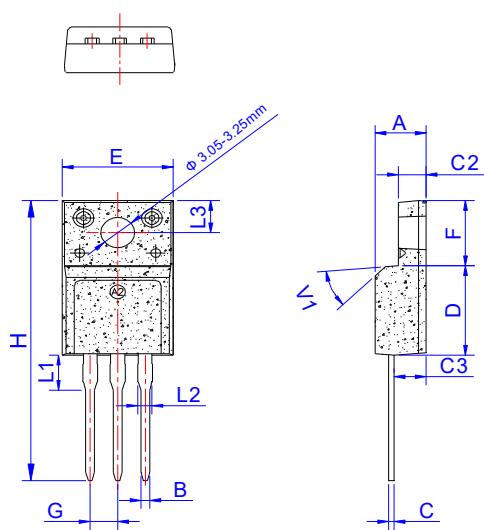
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		I -II-III			
<b>JST16F-1200CW</b>	<b>1200</b>	<b>35</b>	<b>TO-220F(Ins)</b>	<b>50</b>	<b>Tube</b>

**Document Revision History**

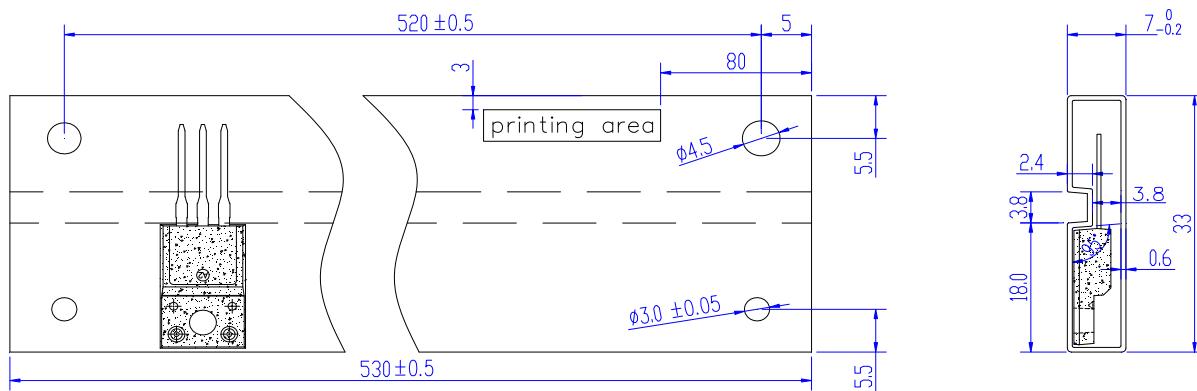
Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated

## PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	3.20		3.80	0.126		0.150
L2	1.14		1.70	0.045		0.067
L3	3.20		3.60	0.126		0.142
V1			45°			45°

## DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220F	TUBE	50	1,000	5,000

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